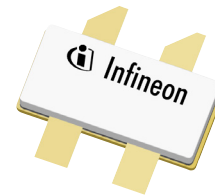


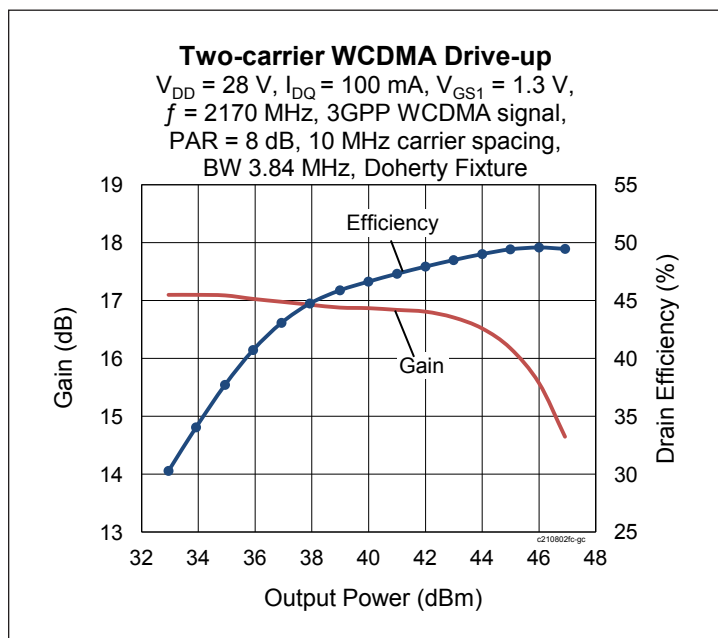
## Thermally-Enhanced High Power RF LDMOS FET 80 W, 28 V, 1805 – 2170 MHz

### Description

The PTAC210802FC is an 80-watt LDMOS FET with an asymmetrical design intended for use in multi-standard cellular power amplifier applications in the 1805 to 2170 MHz frequency band. Features include dual-path design, input matching, high gain and thermally-enhanced package with earless flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTAC210802FC  
Package H-37248-4



### Features

- Asymmetrical design
  - Main: P1dB = 19 W Typ
  - Peak: P1dB = 60 W Typ
- Broadband internal matching
- Wide video bandwidth
- Typical CW pulsed performance, 2170 MHz, 28 V (Doherty fixture)
  - Output power @ P<sub>3dB</sub> = 75 W
  - Efficiency = 48%
  - Gain @ P<sub>3dB</sub> = 14 dB
- Typical CW pulsed performance, 1880 MHz, 28 V (Doherty fixture)
  - Output power @ P<sub>1dB</sub> = 45 W
  - Output power @ P<sub>3dB</sub> = 80 W
  - Efficiency = 48%
  - Gain @ P<sub>3dB</sub> = 14 dB
- Capable of handling 10:1 VSWR @28 V, 80 W (CW) output power
- Integrated ESD protection : Human Body Model, Class 1B (per JESD22-A114)
- Pb-free and RoHS compliant

### RF Characteristics

#### Two-carrier WCDMA Specifications (tested in Infineon Doherty test fixture)

$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 85\text{ mA}$ ,  $V_{GS1} = 1.3\text{ V}$ ,  $P_{OUT} = 5\text{ W avg}$ ,  $f_1 = 2165\text{ MHz}$ ,  $f_2 = 2175\text{ MHz}$ , 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 8 dB @ 0.01% CCDF, 10 MHz carrier spacing

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	15.5	—	17.5	dB
Drain Efficiency	$\eta_D$	39	43	—	%
Intermodulation Distortion	IMD	—	-31	-26	dBc
Output PAR at 0.01% probability on CCDF	OPAR	8	—	—	dB

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

**ESD:** Electrostatic discharge sensitive device—observe handling precautions!

**RF Characteristics** (cont.)

**Two-carrier WCDMA Specifications** (not subject to production test, verified by design/characterization in Infineon)

Doherty test fixture)

 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 150\text{ mA}$ ,  $V_{GS1} = 2\text{ V}$ ,  $P_{OUT} = 5\text{ W avg}$ ,  $f_1 = 1880\text{ MHz}$ ,  $f_2 = 1870\text{ MHz}$ , 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 8 dB @ 0.01% CCDF, 10 MHz carrier spacing

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	17.5	18.3	19.5	dB
Drain Efficiency	$\eta_D$	33.5	36	—	%
Adjacent Channel Power Ratio	ACPR	—	-38	-33	dBc

**DC Characteristics** (each side)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	1	$\mu\text{A}$
	$V_{DS} = 63\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	10	$\mu\text{A}$
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $I_{DQ} = 0\text{ V}$	$I_{GSS}$	—	—	1	V
On-State Resistance	(main) $V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.6	—	$\Omega$
	(peak) $V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.19	—	$\Omega$
Operating Gate Voltage	(main) $V_{DS} = 28\text{ V}$ , $I_{DQ} = 85\text{ mA}$	$V_{GS}$	2.30	2.65	3.0	V
	(peak) $V_{DS} = 28\text{ V}$ , $I_{DQ} = 360\text{ mA}$	$V_{GS}$	2.35	2.70	3.05	V

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	V
Gate-Source Voltage	$V_{GS}$	-6 to +10	V
Operating Voltage	$V_{DD}$	0 to +32	V
Junction Temperature	$T_J$	225	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-65 to +150	$^{\circ}\text{C}$

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range ( $V_{DD}$ ) specified above.

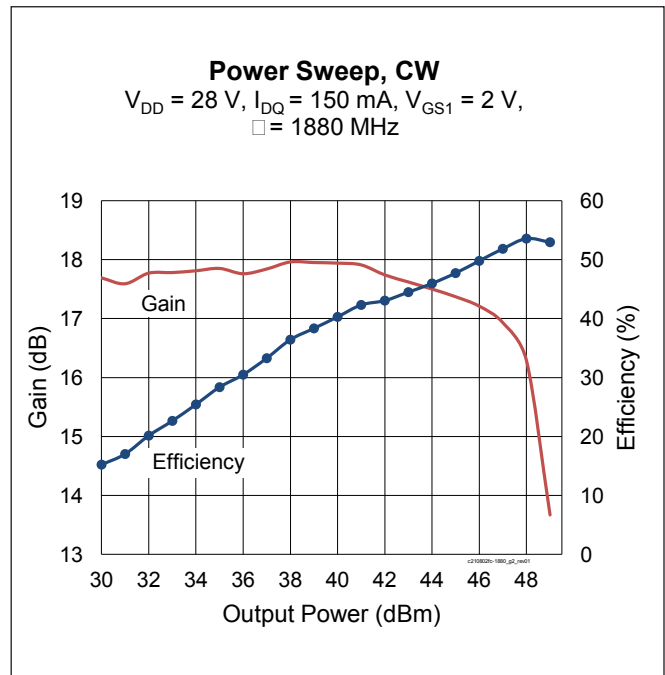
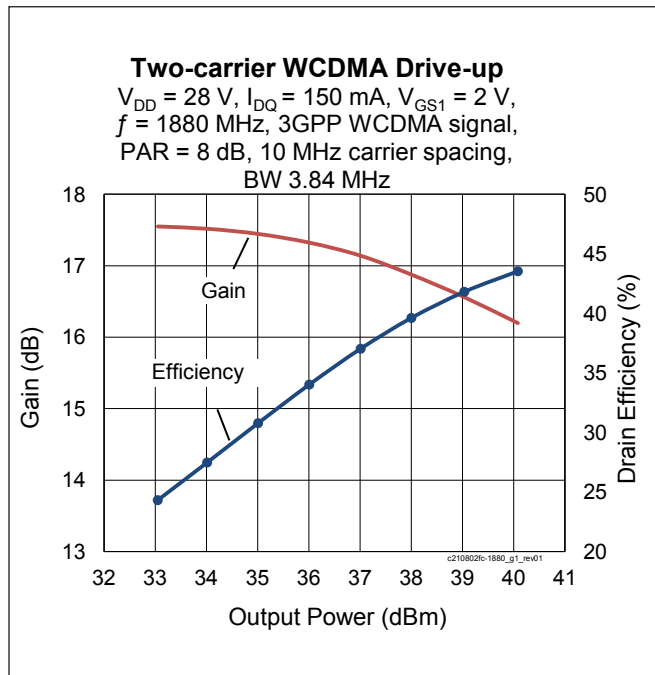
### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance (main) ( $T_{CASE} = 70\text{ }^{\circ}\text{C}$ , 19 W (CW), $V_{DD} = 28\text{ V}$ , $I_{DQ} = 85\text{ mA}$ )	$R_{\theta JC}$	2.5	$^{\circ}\text{C/W}$
Thermal Resistance (peak) ( $T_{CASE} = 70\text{ }^{\circ}\text{C}$ , 60 W (CW), $V_{DD} = 28\text{ V}$ , $I_{DQ} = 360\text{ mA}$ )	$R_{\theta JC}$	0.8	$^{\circ}\text{C/W}$

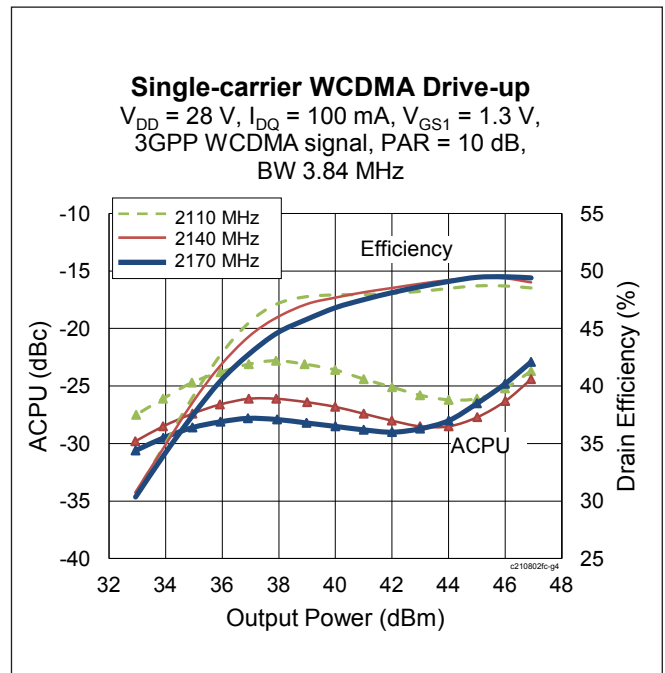
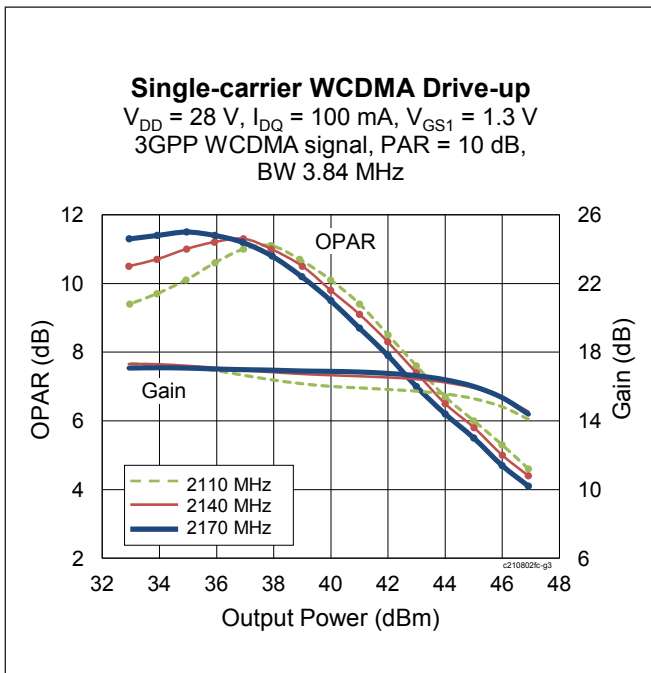
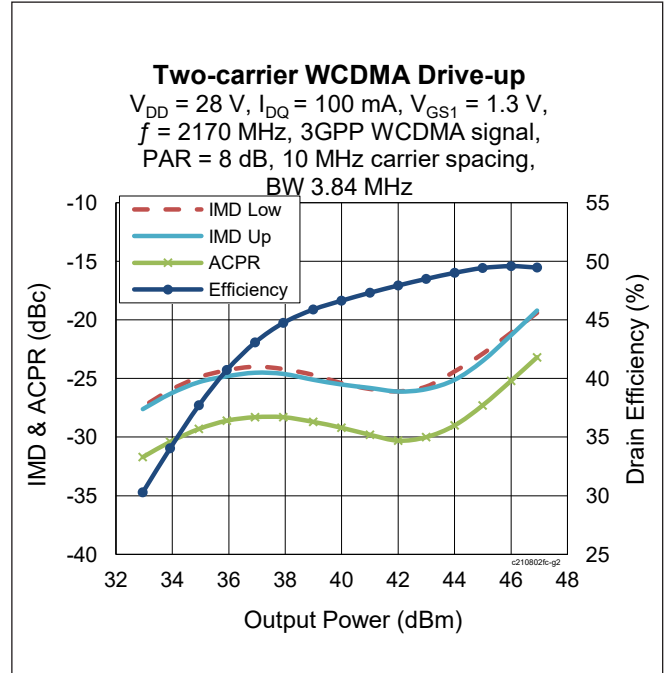
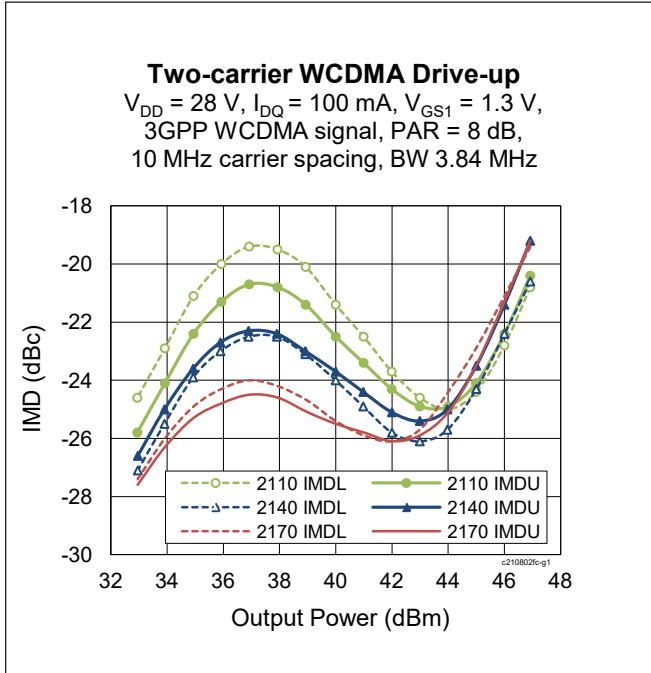
### Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTAC210802FC V1 R0	PTAC210802FCV1R0XTMA1	H-37248-4, earless flange	Tape & Reel, 50 pcs
PTAC210802FC V1 R250	PTAC210802FCV1R250XTMA1	H-37248-4, earless flange	Tape & Reel, 250 pcs
PTAC210802FC V1 S250	PTAC210802FCV1S250XTMA1	H-37248-4, earless flange	Tape & Reel, 250 pcs

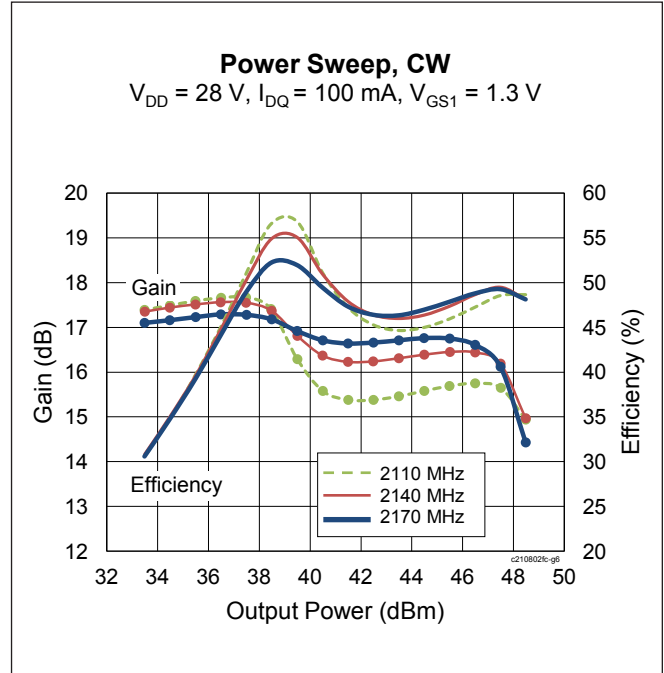
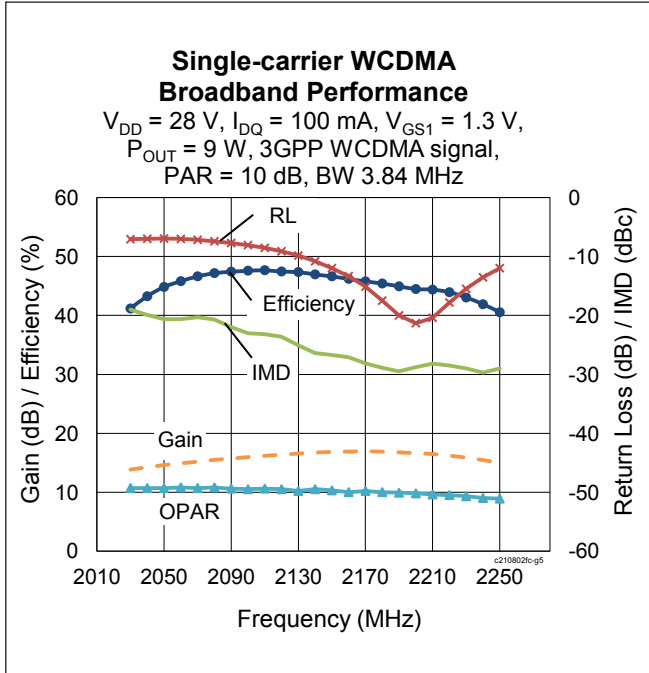
### Typical Performance (data taken in a Doherty test fixture)



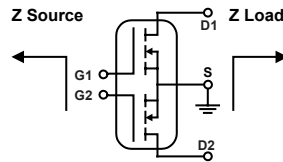
Typical Performance (cont.)



Typical Performance (cont.)



Load Pull Performance



Main Side Load Pull Performance – Pulsed CW signal: 16  $\mu\text{sec}$ , 10% duty cycle;  $V_{DD} = 28\text{ V}$ , 100 mA

Freq [MHz]	$Z_s$ [ $\Omega$ ]	$P_{1dB}$					$P_{3dB}$				
		$Z_l$ [ $\Omega$ ]	Gain [dB]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	PAE [%]	$Z_l$ [ $\Omega$ ]	Gain [dB]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	PAE [%]
2110	28.4 - j28.1	15.1 - j11.9	20.8	43.40	22	50	4.6 - j5.2	23.6	41.3	13	68.1
2140	32.4 - j27.7	7.7 - j10	22.0	43.50	22	61	4.15 - j6	23.9	41.3	13	71.9
2170	45.1 - j33.3	10.8 - j10.6	21.6	43.64	23	58	5.2 - j7.2	23.4	42.1	16	68.6

Peak Side Load Pull Performance – Pulsed CW signal: 16  $\mu\text{sec}$ , 10% duty cycle;  $V_{DD} = 28\text{ V}$ ,  $V_{GS1} = 1.41\text{ V}$ , Doherty Class C

Freq [MHz]	$Z_s$ [ $\Omega$ ]	$P_{1dB}$					$P_{3dB}$				
		$Z_l$ [ $\Omega$ ]	Gain [dB]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	PAE [%]	$Z_l$ [ $\Omega$ ]	Gain [dB]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	PAE [%]
2110	14.8 - j14.6	2.4 - j7.4	14.1	49.60	91	62.0	1.6 - j6.0	15.3	48.3	68	72.5
2140	20.6 - j13.6	2.7 - j7.8	14.0	49.50	89	58.8	1.8 - j6.5	15.2	48.7	74	68.5
2170	24.5 - j9.8	2.6 - j8.1	13.9	49.60	91	57.7	2.0 - j6.6	15.3	48.6	72	67.9

## Reference Circuit

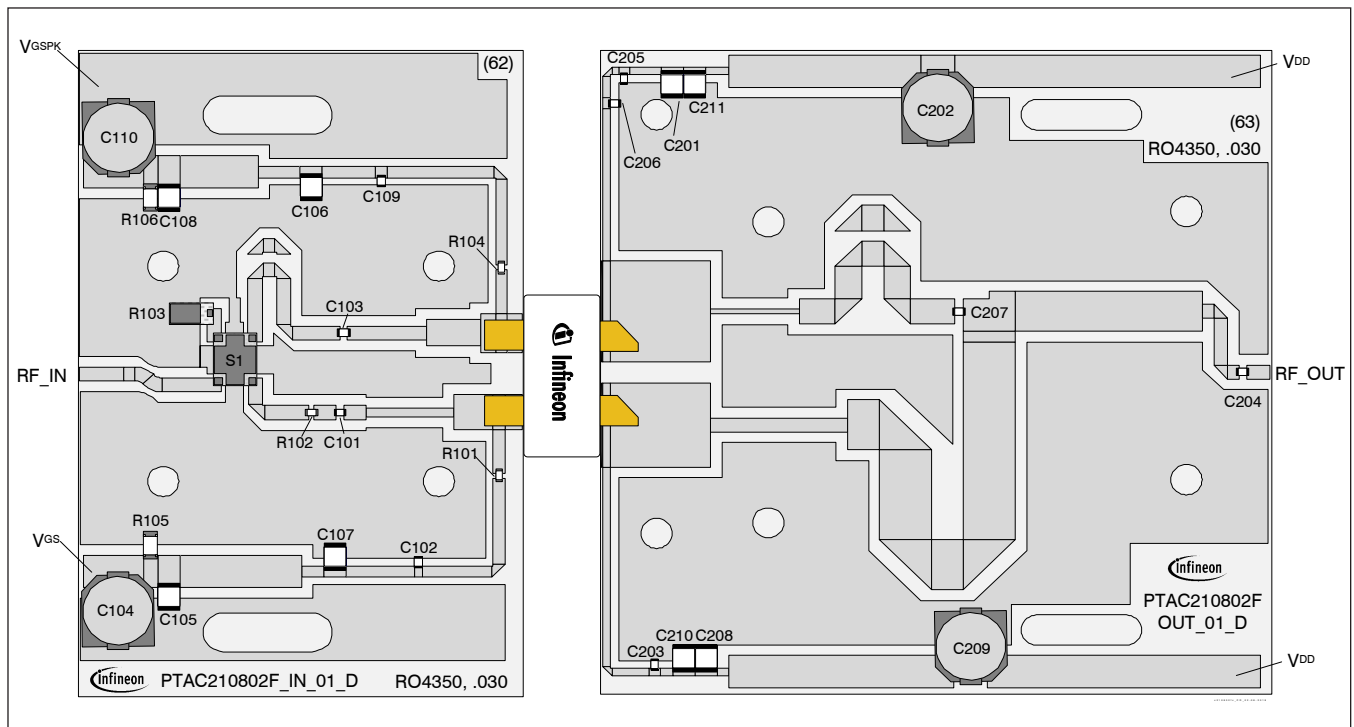
### Reference Circuit Assembly

DUT PTAC210802FC

Test Fixture Part No. LTA/PTAC210802FC

PCB Rogers 4350, 0.762 mm [0.030"] thick, 2 oz. copper,  $\epsilon_r = 3.66$

Find Gerber files for this test fixture on the Infineon Web site at <http://www.infineon.com/rfpower>



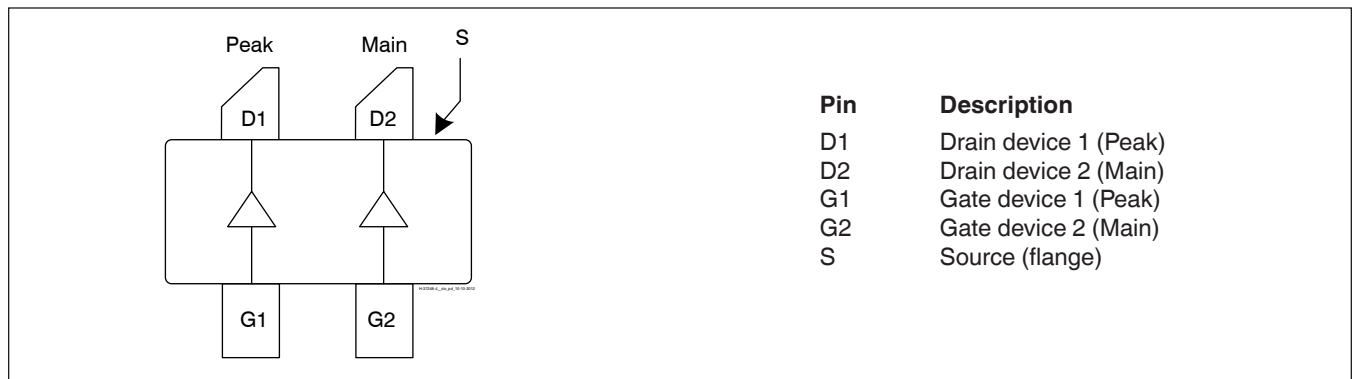
Reference circuit assembly diagram (not to scale)

**Reference Circuit** (cont.)

**Components Information**

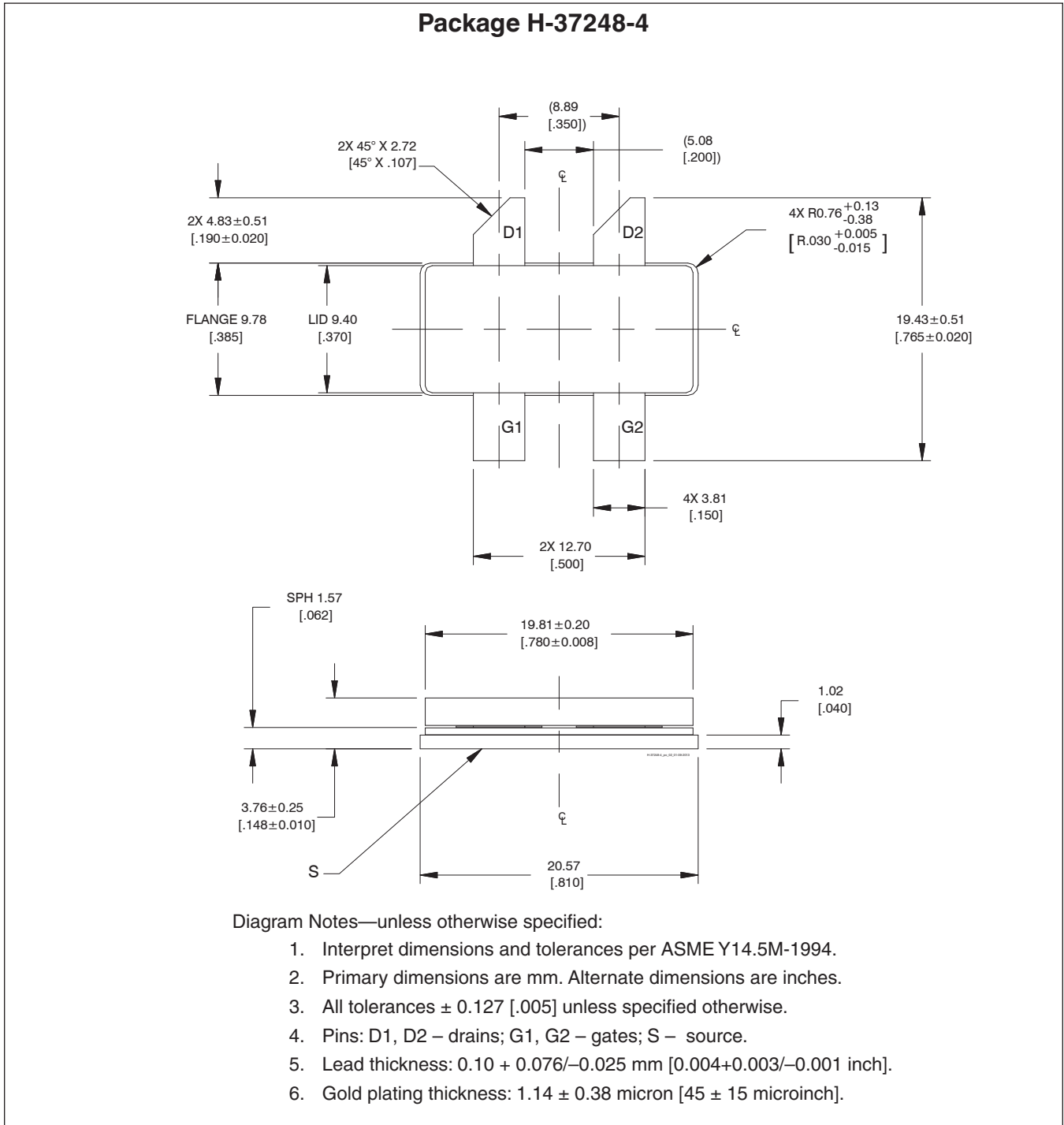
Component	Description	Supplier	P/N
<b>Input</b>			
C101, C102, C103, C109	Chip capacitor, 24 pF	ATC	ATC800A240JT250XB
C104, C110	Capacitor, 100 $\mu$ F	Panasonic Electronic Components	EEE-FP1V101AP
C105, C108	Chip capacitor, 0.1 $\mu$ F	Kemet	C1210C104K5RACTU
C106, C107	Capacitor, 10 $\mu$ F	Taiyo Yuden	UMK325C7106MM-T
R101, R102, R104	Resistor, 10 $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ100V
R103	Resistor, 50 $\Omega$	Anaren	C16A50Z4
R105, R106	Resistor, 1000 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ102V
S1	Hybrid coupler	Anaren	X3C21P1-03S
<b>Output</b>			
C201, C208, C210, C211	Capacitor, 10 $\mu$ F	Taiyo Yuden	UMK325C7106MM-T
C202, C209	Capacitor, 220 $\mu$ F	Panasonic Electronic Components	EEE-FP1V221AP
C203, C204, C205, C206, C207	Chip capacitor, 24 pF	ATC	ATC800A240JT250XB

**Pinout Diagram** (top view)



Lead connections for PTAC210802FC

Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>



## Revision History

Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2013-06-11	Advance	All	Data Sheet reflects advance specification for product development
01.1	2012-06-12	Advance	2	Updated power level measured for thermal data
02	2013-10-17	Production	All	Data Sheet reflects released product specification
03	2013-12-17	Production	1 2 7	Added ESD classification, revised two-carrier WCDMA Specifications Added operating voltage in Maximum Ratings table Updated package outline
04	2014-05-14	Production	2	Revised junction temperature in Maximum Ratings table
05	2014-10-31	Production	1	Revised ESD classification. Corrected IMD to ACPR in RF Characteristics table.
05.1	2015-12-23	Production	2	DC Characteristic Table
05.2	2016-06-17	Production	2	Updated ordering code to include R0
06	2017-04-07	Production	1	Updated RF Characteristics table to include OPAR
06.1	2018-02-08	Production	1, 3	Updated RF Characteristics table and ordering information

### We Listen to Your Comments

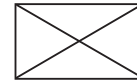
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